	Type	L #	Hits	Search Text	DBs
1	BRS	L1	120	recharge near period	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	13371	gate near pulse	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	248744	low near temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	0	1 and 2 and 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	L5	4	1 and 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L6	1167	345/204.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	L7	1532	345/211-213.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	L8	4417	345/87-92.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	BRS	L9	6814	6 or 7 or 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	L10	178	increase and (recharging adj time)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	BRS	L11	0	9 and 10	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	L12	2557	transistor and (temperature near characteristic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

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	Type	L #	Hits	Search Text	DBs
13	BRS	L13	22561	recharging	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	L14	36	12 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	BRS	L15	109665	LCD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	L16	10	1 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	BRS	L17	9833	TFT and LCD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	BRS	L18	401	recharging adj time	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
19	BRS	L19	1	17 and 18	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

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3	BRS	L3	248744	low near temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	0	1 and 2 and 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
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8	BRS	L8	4417	345/87-92.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	BRS	L9	6814	6 or 7 or 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	L10	178	increase and (recharging adj time)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	BRS	L11	0	9 and 10	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
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19	BRS	L19	1	17 and 18	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
20	BRS	L20	448	circuit near recharge	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
21	BRS	L21	3	3 and 20	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

Type	L #	Hits	Search Text	DBs
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